



USPTO-1449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE INFORMATION DISCLOSURE STATEMENT BY APPLICATION	ATTY. DOCKET NO.:13875-US-PA	APPLICATION NO.: 10/710,199
	APPLICANT: Yang et al.	
	FILING DATE: June 25, 2004	GROUP 2812

U.S. PATENT DOUCMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FIILNG DATE (IF APPROPRIATE)

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	FIILNG DATE (IF APPROPRIATE)

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)
	Michaelson, " The work function of the elements and its periodicity", <i>JOURNAL OF APPLIED PHYSICS</i> , Vol. 48, No. 11, November 1977, pp.4729-4733.
	Zlatanovic et al., " Variation of reflectivity spectra, preferred orientation and stoichiometry of polycrystalline TiN films due to nitrogen flow variation" <i>PROC. 22nd INTERNATIONAL CONFERENCE ON MICROELECTRONICS (MIEL 2000)</i> , Vol. 1, NIS, SERBIA, 14-17, May 2000, pp. 261-264.
	Farahani et al. , " Limitation of the Tin/ Ti layer formed by the rapid thermal heat treatment of pure Ti films in an NH ₃ ambient in fabrication of submicrometer CMOS flash EPROM IC's" , <i>IEEE TRANSACTIONS ON SEMICONDUCTOR MANUFACTURING</i> , Vol. 10, No. 1, February 1997, pp.147-153.
	Abe et al. " Cu damascene interconnects with crystallographic texture control and its electromigration performance", <i>IEEE 98CH36173. 36th ANNUAL INTERNATIONAL RELIABILITY PHYSICS SYMPOSIUMS</i> , RENO, NEVADA, 1998, pp.342-347.
	Sun et al. " A comparative study of CVD TiN and CVD TaN diffusion barriers for copper interconnection", 1995, pp. 18. 5.1-18. 5. 4.

EXAMINER	<i>Dh</i>	DATE CONSIDERED	<i>12/2005</i>
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